

# DDR3 Registered/ECC DIMM Module

**4GB based on 2Gbit component**

**82FBGA with Pb-Free**



**Revision 1.0 (May, 2008)**  
-Initial Release

**1.0 Feature**

- JEDEC standard  $V_{DDQ}=1.5V \pm 0.075V$  Power Supply
- $V_{DDQ} = 1.5V \pm 0.075V$
- Programmable CAS Latency: 6,7,8,9,10,11
- Programmable Additive Latency(Posted CAS) : 0, CL - 2, or CL - 1 clock
- Programmable CAS Write Latency(CWL) = 5(DDR3-800), 6(DDR3-1066), 7(DDR3-1333) and 8(DDR3-1600)
- 400MHz fCK for 800Mb/sec/pin, 533MHz fCK for 1066Mb/sec/pin, 667MHz fCK for 1333Mb/sec/pin, 800MHz fCK for 1600Mb/sec/pin
- 8-bit pre-fetch
- Burst Length: 8 (Interleave without any limit, sequential with starting address “000” only), 4 with tCCD = 4 which does not allow seamless read or write [either On the fly using A12 or MRS]
- Internal(self) calibration : Internal self calibration through ZQ pin (RZQ : 240 ohm  $\pm$  1%)
- Bi-directional Differential Data Strobe
- Asynchronous Reset
- On-Die termination using ODT pin
- 8 independent internal bank
- Average Refresh Period 7.8us at lower than a TCASE 85°C, 3.9us at 85°C < TCASE < 95 °C
- Serial presence detect with EEPROM
- RDIMM Dimension (Nominal) 30.00 mm high, 133.35 mm wide
- Based on JEDEC standard reference Raw Cards Lay out.
- RoHS compliant
- Gold plated contacts

**2.0 Ordering Information**

Part number	Density	Module Organization	Component composition	Component PKG	Module Rank	Description
W16RB4G8M	4GB	512Mx72	256Mx8*18	FBGA	2	PC3-12800

Note: Last Character of the Part Number representing DRAM vendor  
S=Samsung; M=Micron; H=Hynix

**3.0 Operating Frequencies**

	DDR3-1600	Unit
CL-tRCD-tRP	11-11-11	tCK
CAS Latency	11	tCK
tCK(min)	1.25	ns
tRCD(min)	13.5	ns
tRP(min)	13.5	ns
tRAS(min)	35	ns
tRC(min)	48.75	ns

**4.0 Absolute Maximum DC Rating**

Symbol	Parameter	Rating	Units
$V_{in}, V_{out}$	Voltage on any pin relative to $V_{SS}$	-0.4 ~ 1.975	V
$V_{DD}$	Voltage on $V_{DD}$ & $V_{DDQ}$ supply relative to $V_{SS}$	-0.4 ~ 1.975	V
$V_{DDQ}$	Short circuit current	-0.4 ~ 1.975	V
$V_{DDL}$	Power dissipation	-0.4 ~ 1.975	V
$T_{STG}$	Storage Temperature	-55 ~ + 100	°C

**5.0 DIMM Pin Configurations (Front side/Back side)**

Pin	Front	Pin	Back	Pin	Front	Pin	Back	Pin	Front	Pin	Back	Pin	Front	Pin	Back
1	V <sub>REFDQ</sub>	121	V <sub>SS</sub>	31	DQ25	151	V <sub>SS</sub>	61	A2	181	A1	91	DQ41	211	V <sub>SS</sub>
2	V <sub>SS</sub>	122	DQ4	32	V <sub>SS</sub>	152	DQS12	62	V <sub>DD</sub>	182	V <sub>DD</sub>	92	V <sub>SS</sub>	212	DQS14
3	DQ0	123	DQ5	33	$\overline{\text{DQS3}}$	153	$\overline{\text{DQS12}}$	63	NC	183	V <sub>DD</sub>	93	$\overline{\text{DQS5}}$	213	$\overline{\text{DQS14}}$
4	DQ1	124	V <sub>SS</sub>	34	DQS3	154	V <sub>SS</sub>	64	NC	184	CK0	94	DQS5	214	V <sub>SS</sub>
5	V <sub>SS</sub>	125	DQS9	35	V <sub>SS</sub>	155	DQ30	KEY				95	V <sub>SS</sub>	215	DQ46
6	$\overline{\text{DQS0}}$	126	$\overline{\text{DQS9}}$	36	DQ26	156	DQ31	65	V <sub>DD</sub>	185	$\overline{\text{CK0}}$	DQ47	DQ42	216	DQ47
7	DQS0	127	V <sub>SS</sub>	37	DQ27	157	V <sub>SS</sub>	66	V <sub>DD</sub>	186	V <sub>DD</sub>	97	DQ43	217	V <sub>SS</sub>
8	V <sub>SS</sub>	128	DQ6	38	V <sub>SS</sub>	158	CB4	67	V <sub>REFCA</sub>	187	$\overline{\text{EVENT}}$	98	V <sub>SS</sub>	218	DQ52
9	DQ2	129	DQ7	39	CB0	159	CB5	68	NC/Par_in	188	A0	99	DQ48	219	DQ53
10	DQ3	130	V <sub>SS</sub>	40	CB1	160	V <sub>SS</sub>	69	V <sub>DD</sub>	189	V <sub>DD</sub>	100	DQ49	220	V <sub>SS</sub>
11	V <sub>SS</sub>	131	DQ12	41	V <sub>SS</sub>	161	DQS17	70	A10/AP	190	BA1	101	V <sub>SS</sub>	221	DQS15
12	DQ8	132	DQ13	42	$\overline{\text{DQS8}}$	162	$\overline{\text{DQS17}}$	71	BA0	191	V <sub>DD</sub>	102	$\overline{\text{DQS6}}$	222	$\overline{\text{DQS15}}$
13	DQ9	133	V <sub>SS</sub>	43	DQS8	163	V <sub>SS</sub>	72	V <sub>DD</sub>	192	$\overline{\text{RAS}}$	103	DQS6	223	V <sub>SS</sub>
14	V <sub>SS</sub>	134	DQS10	44	V <sub>SS</sub>	164	CB6	73	$\overline{\text{WE}}$	193	$\overline{\text{S0}}$	104	V <sub>SS</sub>	224	DQ54
15	$\overline{\text{DQS1}}$	135	$\overline{\text{DQS10}}$	45	CB2	165	CB7	74	$\overline{\text{CAS}}$	194	V <sub>DD</sub>	105	DQ50	225	DQ55
16	DQS1	136	V <sub>SS</sub>	46	CB3	166	V <sub>SS</sub>	75	V <sub>DD</sub>	195	ODT0	106	DQ51	226	V <sub>SS</sub>
17	V <sub>SS</sub>	137	DQ14	47	V <sub>SS</sub>	167	NC	76	NC	196	A13	107	V <sub>SS</sub>	227	DQ60
18	DQ10	138	DQ15	48	V <sub>TT</sub>	168	$\overline{\text{RESET}}$	77	NC	197	V <sub>DD</sub>	108	DQ56	228	DQ61
19	DQ11	139	V <sub>SS</sub>	49	V <sub>TT</sub>	169	NC	78	V <sub>DD</sub>	198	NC	109	DQ57	229	V <sub>SS</sub>
20	V <sub>SS</sub>	140	DQ20	50	CKE0	170	V <sub>DD</sub>	79	NC	199	V <sub>SS</sub>	110	V <sub>SS</sub>	230	DQS16
21	DQ16	141	DQ21	51	V <sub>DD</sub>	171	A15	80	V <sub>SS</sub>	200	DQ36	111	$\overline{\text{DQS7}}$	231	$\overline{\text{DQS16}}$
22	DQ17	142	V <sub>SS</sub>	52	BA2	172	A14	81	DQ32	201	DQ37	112	DQS7	232	V <sub>SS</sub>
23	V <sub>SS</sub>	143	DQS11	53	$\overline{\text{ERR\_OUT}}$	173	V <sub>DD</sub>	82	DQ33	202	V <sub>SS</sub>	113	V <sub>SS</sub>	233	DQ62
24	$\overline{\text{DQS2}}$	144	$\overline{\text{DQS11}}$	54	V <sub>DD</sub>	174	A12	83	V <sub>SS</sub>	203	DQS13	114	DQ58	234	DQ63
25	DQS2	145	V <sub>SS</sub>	55	A11	175	A9	84	$\overline{\text{DQS4}}$	204	DQS13	115	DQ59	235	V <sub>SS</sub>
26	V <sub>SS</sub>	146	DQ22	56	A7	176	V <sub>DD</sub>	85	DQS4	205	V <sub>SS</sub>	116	V <sub>SS</sub>	236	V <sub>DD</sub> SPD
27	DQ18	147	DQ23	57	V <sub>DD</sub>	177	A8	86	V <sub>SS</sub>	206	DQ38	117	SA0	237	SA1
28	DQ19	148	V <sub>SS</sub>	58	A5	178	A6	87	DQ34	207	DQ39	118	SCL	238	SDA
29	V <sub>SS</sub>	149	DQ28	59	A4	179	V <sub>DD</sub>	88	DQ35	208	V <sub>SS</sub>	119	SA2	239	V <sub>SS</sub>
30	DQ24	150	DQ29	60	V <sub>DD</sub>	180	A3	89	V <sub>SS</sub>	209	DQ44	120	V <sub>TT</sub>	240	V <sub>TT</sub>
								90	DQ40	210	DQ45				

**6.0 DIMM Pin Description**

Pin Name	Function	Pin Name	Function
A0 ~ A15	Address input (Multiplexed)	ODT0~ODT1	On Die Termination
A10/AP	Address Input/Auto pre-charge	CB0~CB7	ECC Data check bits Input/Output
BA0 ~ BA2	Bank Select	DQ0~DQ63	Data Input/Output
$\overline{CK0} \sim \overline{CK2}$ , CK0~CK2	Clock input	$\overline{DQS0} \sim \overline{DQS8}$	Data strobes, negative line
CKE0, CKE1	Clock enable input	DM (0~8),	Data Masks/Data strobes (Read)
$\overline{S0}$ , $\overline{S1}$	Chip select input	DQS0~DQS8	Data Strobes
$\overline{RAS}$	Row address strobe	RFU	Reserved for future used
$\overline{CAS}$	Column address strobe	V <sub>TT</sub>	SDRAM I/O termination power supply
$\overline{WE}$	Write Enable	TEST	Memory bus test tool
SCL	SPD Clock Input	V <sub>DD</sub>	Core Power
SDA	SPD Data Input/Output	V <sub>DDQ</sub>	I/O Power
SA0~SA2	SPD Address	V <sub>SS</sub>	Ground
Par_In	Parity bit for address & Control bus	V <sub>REFDQ</sub>	SDRAM Input/Output Reference Supply
$\overline{EVENT}$	EVENT pin on TS/SPD part, Temperature event	V <sub>DDSPD</sub>	Serial EEPROM Power Supply
Reset	Register and PLL control pin	V <sub>REFCA</sub>	Command Address Reference Supply

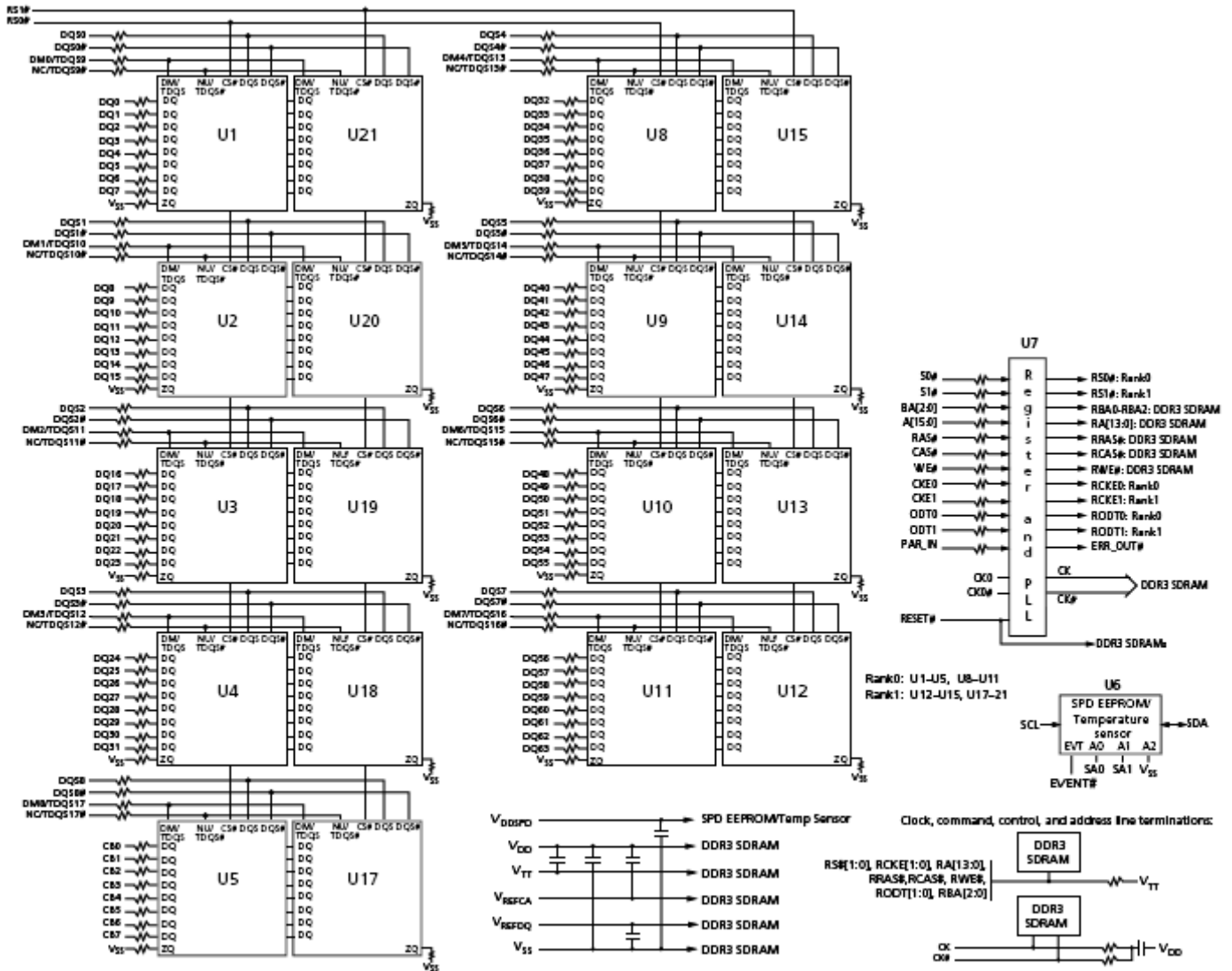
**7.0 Address Configuration**

Organization	Row Address	Column Address	Bank Address	Auto Pre-charge
256Mx8(2Gb)base	A0-A14	A0-A9	BA0-BA2	A10

## 240-Pin DDR3- Reg/ECC-DIMM

## DDR3 SDRAM

### 8.0 Functional Block Diagram: 4GB; 512x72 Module (Populated as 2 ranks of x8 SDRAM Module)



Note: 1. The ZQ ball on each DDR3 component is connected to an external  $240\Omega \pm 1$  percent resistor that is tied to ground. It is used for the calibration of the component's ODT and output driver.

**9.0 AC & DC Operating Conditions**

Recommended operating conditions (Voltage referenced to V<sub>SS</sub>=0V, TA=0 to 70°C)

Symbol	Parameter	Min	Typ	Max	Unit
V <sub>DD</sub>	Supply Voltage	1.425	1.5	1.575	V
V <sub>DDQ</sub>	Supply Voltage for Output	1.425	1.5	1.575	V
V <sub>REFDQ(DC)</sub>	I/O Reference Voltage (DQ)	0.49*V <sub>DDQ</sub>	0.50*V <sub>DDQ</sub>	0.51*V <sub>DDQ</sub>	V
V <sub>REFCA(DC)</sub>	I/O Reference Voltage (CMD/Add)	0.49*V <sub>DDQ</sub>	0.50*V <sub>DDQ</sub>	0.51*V <sub>DDQ</sub>	V
V <sub>TT</sub>	Termination Voltage	0.49*V <sub>DDQ</sub>	0.50*V <sub>DDQ</sub>	0.51*V <sub>DDQ</sub>	V

**10.0 Capacitance (Max.)**

Symbol	Parameter/Condition	Min	Max	Unit
CCK	Input capacitance, CK and $\overline{CK}$	-	11	pF
CI1	Input capacitance, CKE and $\overline{CS}$	-	12	pF
CI2	Input capacitance, Addr, RAS, CAS, $\overline{WE}$	-	12	pF
CIO	Input capacitance, DQ, DM, DQS, $\overline{DQS}$	-	10	pF

**11.1 AC Timing Parameters & Specifications**

(AC operating conditions unless otherwise noted)

Parameter	Symbol	DDR3-1600		Units
		min	max	
Minimum Clock Cycle Time (DLL off mode)	tCK(DLL_OFF)	8	-	ns
Average Clock Period	tCK(avg)	-		ps
Clock Period	tCK(abs)	tCK(avg) min +tJIT(per)min	tCK(avg) max +tJIT(per)max	ps
Average high pulse width	tCH(avg)	0.47	0.53	tCK(avg)
Average low pulse width	tCL(avg)	0.47	0.53	tCK(avg)
Clock Period Jitter	tJIT(per)	-70	70	ps
Clock Period Jitter during DLL locking period	tJIT(per, lck)	-60	60	ps
Cycle to Cycle Period Jitter	tJIT(cc)	140	-	ps
Cycle to Cycle Period Jitter during DLL locking period	tJIT(cc, lck)	120	-	ps
Cumulative error across 2 cycles	tERR(2per)	- 103	103	ps
Cumulative error across 3 cycles	tERR(3per)	- 122	122	ps
Cumulative error across 4 cycles	tERR(4per)	- 136	136	ps
Cumulative error across 5 cycles	tERR(5per)	- 147	147	ps
Cumulative error across 6 cycles	tERR(6per)	- 155	155	ps
Cumulative error across 7 cycles	tERR(7per)	- 163	163	ps
Cumulative error across 8 cycles	tERR(8per)	- 169	169	ps
Cumulative error across 9 cycles	tERR(9per)	- 175	175	ps
Cumulative error across 10 cycles	tERR(10per)	- 180	180	ps

**11.2 AC Timing Parameters & Specifications (con't)**

Parameter	Symbol	DDR3-1600		Units
		min	max	
Cumulative error across 11 cycles	tERR(11per)	- 184	184	ps
Cumulative error across 12 cycles	tERR(12per)	- 188	188	ps
Cumulative error across n = 13, 14 ... 49, 50 cycles	tERR(nper)	tERR(nper)min = (1 + 0.68ln(n))*tJIT(per)min tERR(nper)max = (1 = 0.68ln(n))*tJIT(per)max		ps
Absolute clock HIGH pulse width	tCH(abs)	0.43	-	tCK(avg)
Absolute clock Low pulse width	tCL(abs)	0.43	-	tCK(avg)
<b>Data Timing</b>				
DQS, /DQS to DQ skew, per group, per access	tDQSQ	-	100	ps
DQ output hold time from DQS, /DQS	tQH	0.38	-	tCK(avg)
DQ low-impedance time from CK, /CK	tLZ(DQ)	-450	225	ps
DQ high-impedance time from CK, /CK	tHZ(DQ)	-	225	ps
Data setup time to DQS, /DQS referenced to Vih(ac)Vil(ac) levels	tDS(base) AC175	TBD	-	ps
	tDS(base) AC150	10	-	ps
Data hold time to DQS, /DQS referenced to Vih(ac)Vil(ac) levels	tDH(base) DC100	45	-	ps
DQ and DM Input pulse width for each input	tDIPW	360	-	ps
<b>Data Strobe Timing</b>				
DQS, /DQS READ Preamble	tRPRE	0.9	-	tCK
DQS, /DQS differential READ Postamble	tRPST	0.3	-	tCK
DQS, /DQS output high time	tQSH	0.4	-	tCK(avg)
DQS, /DQS output low time	tQSL	0.4	-	tCK(avg)
DQS, /DQS WRITE Preamble	tWPRE	0.9	-	tCK
DQS, /DQS WRITE Postamble	tWPST	0.3	-	tCK
DQS, /DQS rising edge output access time from rising CK, /CK	tDQSCK	-225	225	ps
DQS, /DQS low-impedance time (Referenced from RL-1)	tLZ(DQS)	-450	225	ps
DQS, /DQS high-impedance time (Referenced from RL+BL/2)	tHZ(DQS)	-	225	ps
DQS, DQS differential input low pulse width	tDQSL	0.45	0.55	tCK
DQS, DQS differential input high pulse width	tDQSH	0.45	0.55	tCK
DQS, DQS rising edge to CK, /CK rising edge	tDQSS	-0.27	0.27	tCK(avg)
DQS,DQS falling edge setup time to CK, /CK rising edge	tDSS	0.18	-	tCK(avg)
DQS,DQS falling edge hold time to CK, /CK rising edge	tDSH	0.18	-	tCK(avg)
DLL locking time	tDLLK	512	-	nCK
internal READ Command to PRECHARGE Command delay	tRTP	max (4tCK,7.5ns)	-	
Delay from start of internal write transaction to internal read command	tWTR	max (4tCK,7.5ns)	-	
WRITE recovery time	tWR	15	-	ns
Mode Register Set command cycle time	tMRD	4	-	nCK
Mode Register Set command update delay	tMOD	max (12tCK,15ns)	-	
CAS# to CAS# command delay	tCCD	4	-	nCK
Auto precharge write recovery + precharge time	tDAL(min)	WR + roundup (tRP / tCK(AVG))		nCK

**11.3 AC Timing Parameters & Specifications (con't)**

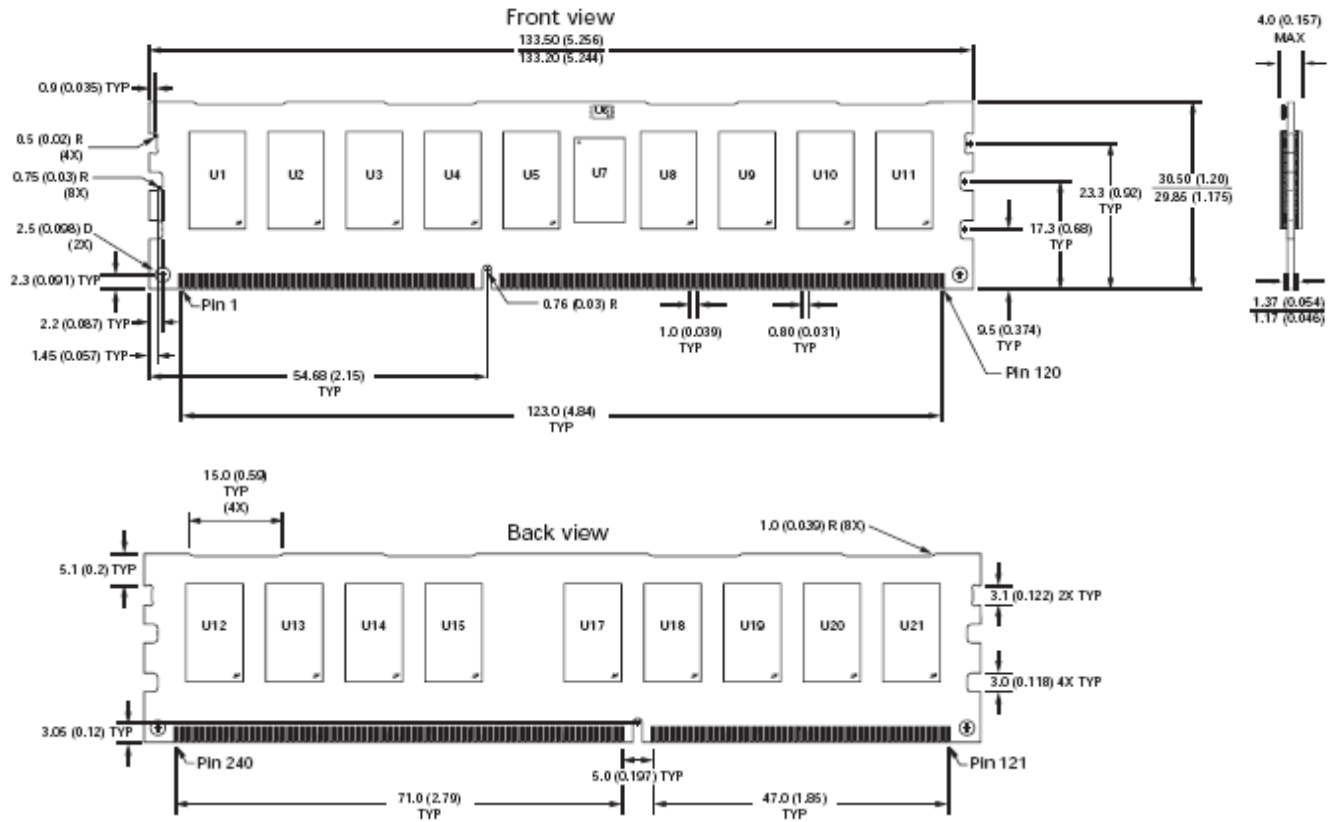
Parameter	Symbol	DDR3-1600		Units
		min	max	
Multi-Purpose Register Recovery Time	tMPRR	1	-	nCK
ACTIVE to PRECHARGE command period	tRAS	36	70,000	ns
ACTIVE to ACTIVE command period for 1KB page size	tRRD	max (4tCK,6ns)	-	
ACTIVE to ACTIVE command period for 2KB page size	tRRD	max (4tCK,7.5ns)	-	
Four activate window for 1KB page size	tFAW	30	-	ns
Four activate window for 2KB page size	tFAW	40	-	ns
Command and Address setup time to CK, /CK referenced to Vih(ac) / Vil(ac) levels	tIS(base) AC175	45	-	ps
	tIS(base) AC150	45+125	-	ps
Command and Address hold time from CK, /CK referenced to Vih(ac) / Vil(ac) levels	tIH(base) DC100	120	-	ps
Control & Address Input pulse width for each input	tIPW	560	-	ps
<b>Calibration Timing</b>				
Power-up and RESET calibration time	tZQinitl	512	-	tCK
Normal operation Full calibration time	tZQoper	256	-	tCK
Normal operation short calibration time	tZQCS	64	-	tCK
<b>Reset Timing</b>				
Exit Reset from CKE HIGH to a valid command	tXPR	max(5tCK, tRFC+ 10ns)	-	
<b>Self Refresh Timing</b>				
Exit Self Refresh to commands not requiring a locked DLL	tXS	max(5tCK, tRFC+ 10ns)	-	
Exit Self Refresh to commands requiring a locked DLL	tXSDLL	tDLLK(min)	-	nCK
Minimum CKE low width for Self refresh entry to exit timing	tCKESR	tCKE(min) + 1tCK	-	
Valid Clock Requirement after Self Refresh Entry (SRE)	tCKSRE	max(5tCK, 10ns)	-	
Valid Clock Requirement before Self Refresh Exit (SRX)	tCKSRX	max(5tCK, 10ns)	-	
<b>Power Down Timing</b>				
Exit Power Down with DLL on to any valid command; Exit Precharge Power Down with DLL frozen to commands not requiring a locked DLL	tXP	max (3tCK,6ns)	-	
Exit Precharge Power Down with DLL frozen to commands requiring a locked DLL	tXPDLL	max(10tCK, 24ns)	-	
CKE minimum pulse width	tCKE	max(3tCK, 5 ns)	-	
Command pass disable delay	tCPDED	1	-	nCK
Power Down Entry to Exit Timing	tPD	tCKE(min)	9*tREFI	tCK
Timing of ACT command to Power Down entry	tACTPDEN	1	-	nCK
Timing of PRE command to Power Down entry	tPRPDEN	1	-	nCK
Timing of RD/RDA command to Power Down entry	tRDPDEN	RL + 4 + 1	-	
Timing of WR command to Power Down entry (BL8OTF, BL8MRS, BL4OTF)	tWRPDEN	WL + 4 + (tWR/tCK)	-	nCK
Timing of WRA command to Power Down entry (BL8OTF, BL8MRS, BL4OTF)	tWRAPDEN	WL + 4 + WR+1	-	nCK
Timing of WR command to Power Down entry (BL4MRS)	tWRPDEN	WL + 2 + (tWR/ tCK(avg))	-	nCK



**11.4 AC Timing Parameters & Specifications (con't)**

Parameter	Symbol	DDR3-1600		Units
		min	max	
Timing of WRA command to Power Down entry(BL4MRS)	tWRAPDEN	WL +2 +WR +1	-	nCK
Timing of REF command to Power Down entry	tREFPDEN	1	-	
Timing of MRS command to Power Down entry	tMRSPDEN	tMOD(min)	-	
<b>ODT Timing</b>				
ODT high time without write command or with write command and BC4	ODTH4	4	-	nCK
ODT high time with Write command and BL8	ODTH8	6	-	nCK
Asynchronous RTT turn-on delay (Power-Down with DLL frozen)	tAONPD	2	8.5	ns
Asynchronous RTT turn-off delay (Power-Down with DLL frozen)	tAOFPD	2	8.5	ns
ODT turn-on	tAON	-225	225	ps
RTT_NOM and RTT_WR turn-off time from ODTL off reference	tAOF	0.3	0.7	tCK(avg)
RTT dynamic change skew	tADC	0.3	0.7	tCK(avg)
<b>Write Leveling Timing</b>				
First DQS pulse rising edge after tDQSS margining mode is programmed	tWLMRD	40	-	tCK
DQS/DQS delay after tDQS margining mode is programmed	tWLDQSEN	25	-	tCK
Setup time for tDQSS latch	tWLS	165	-	ps
Hold time of tDQSS latch	tWLH	165	-	ps
Write leveling output delay	tWLO	0	7.5	ns
Write leveling output error	tWLOE	0	2	ns

**12.0 Physical Dimensions: (256Mx8 Based)  
512Mx72 (2 Ranks)**



Tolerances:  $\pm 0.005(.13)$  unless otherwise specified